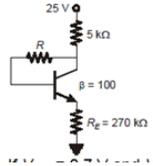


# MSMF GATE CENTRE

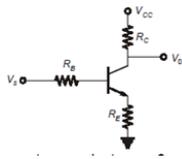
## ANALOG CIRCUITS - 2

- Which configuration of the transistor is used as an impedance transformer ?  
a) Common base      b) Common collector      c) Common emitter      d) Cascade connection
- Consider the circuit shown below



If  $V_{BE} = 0.7V$  and  $V_{CE} = 5V$  then the value of R is

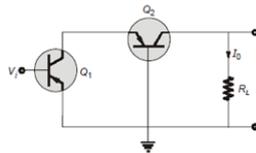
- $6.34M\Omega$
  - $5.97k\Omega$
  - $5.97M\Omega$
  - $6.34k\Omega$
- A small resistance  $R_E$  is introduced in a common emitter bipolar junction transistor amplifier.



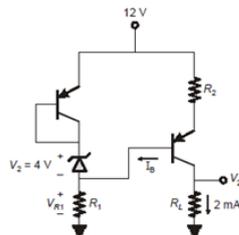
$g_m$  = transconductance,  $\beta$  = current gain

Which of the following statements is not true ?

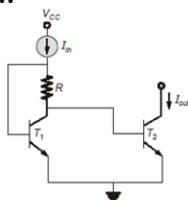
- The small signal voltage gain from collector to base is reduced by a factor of  $(1 + g_m R_E)$
  - High frequency response is significantly improved.
  - The overall gain dependency on  $\beta$  is less
  - Input resistance remains same.
- In the 2 stage amplifier circuit shown in figure, if the transconductance of transistor  $Q_1$  and  $Q_2$  are  $g_{m1}$  and  $g_{m2}$  respectively, the overall transconductance  $g_{m0} = \frac{I_0}{V_1}$  is



- $g_{m0} \equiv g_{m1}$
  - $g_{m0} \equiv g_{m2}$
  - $g_{m0} = g_{m1} + g_{m2}$
  - $g_{m0} = g_{m1} - g_{m2}$
- For the given circuit shown below,  $\beta = 100$  for both transistor  $V_{EB} = 0.7V$  and  $I_z = 5mA$ . The value of  $R_1$  is \_\_\_\_\_  $k\omega$



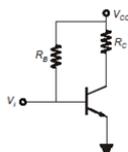
- In the figure shown below



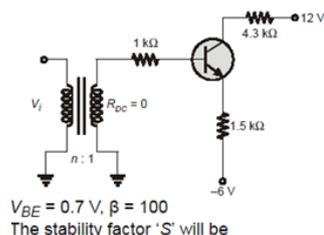
Assuming  $V_T = 25\text{mV}$  and  $I_{in} = 2\text{mA}$ , then the value R that should be used in the circuit so that the output current is half of the input current is \_\_\_\_\_  $\Omega$

(Assume both the transistors to be identical and  $\beta$  of the transistors to be high)

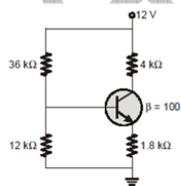
7. Consider a fixed biased circuit with a Q point (9.2 mA, 3.4V). The transistor has a DC current gain of 115. Given that  $V_{BE} = 0.7$  volts and  $V_{CC} = 5\text{Volts}$ . The value of base resistance is \_\_\_\_\_  $k\Omega$



8. In the circuit shown below the transformer and transistor are ideal

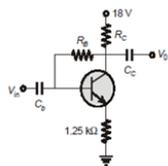


- a) 1.5                      b) 1.66                      c) 1.33                      d) 1
9. For an  $n-p-n$  BJT, the following parameters are given
- $g_m = 40\text{mA/V}$   
 $C_\mu = 2 \times 10^{-14}\text{F}$   
 $C_\pi = 4 \times 10^{-13}\text{F}$   
 Magnitude of midband DC current gain = 100  
 The  $\beta$  cut-off frequency  $f_\beta$  is
- a) 0.152 GHz              b) 15.2 GHz              c) 0.95 GHz              d) 0.019 GHz
10. A Si transistor is biased in potential divider configuration as shown below.



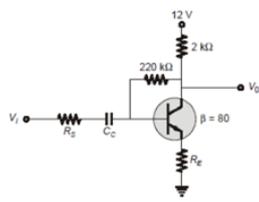
If  $\beta$  is increased by 100%, then  $I_C$  will be

- a) Increased by 4.8%      b) Decreased by 5.7%      c) Increased by 2.9%      d) Increased by 1.0%
11. In the circuit shown below, transistor has a current gain of 200 and base to emitter voltage 0.7 V.



If the transistor is operating at (10V, 2mA) then the resistance  $R_C$  required is

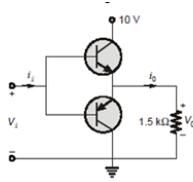
- a) 2.73kΩ                      b) 5.20kΩ                      c) 1.92kΩ                      d) 3.46kΩ
12. Consider the diagram given below



If the transistor is biased with collector to emitter voltage of 5V, then the value of  $R_E$  required is (Assume  $V_{BE} = 0.7V$ )

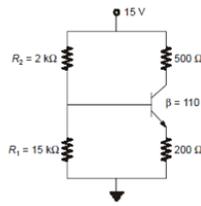
- a)  $2.42k\Omega$                       b)  $4.84k\Omega$                       c)  $1.86k\Omega$                       d)  $5.92k\Omega$

13. Consider the circuit given below



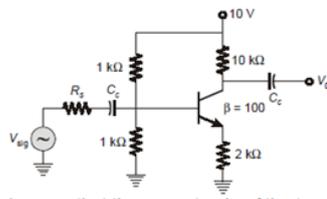
The hybrid parameter for both the transistors are same,  $h_{io} = 1.2k\Omega$ , the  $h_{io} = 99$ ,  $h_{10}$  &  $h_{00}$  are negligible. The current gain  $i_0 / i_1$  is \_\_\_\_\_

14. Consider the circuit shown below



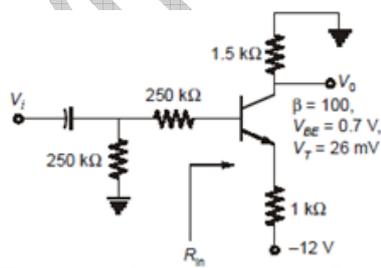
It was found later after calculations that because of a poor solder joint, resistor  $R_1 = 15k$  become open circuit. Assuming  $V_{CE(sat)} = 0$ ,  $V_{BEQ} = 0.7V$  and  $I_{CQ} \approx I_{EQ}$  the change in the  $I_{CQ}$  between the two cases will be \_\_\_\_\_ mA

15. Consider the amplifier circuit shown below



Assume that the current gain of the transistor is very large, then the modulus of the voltage gain of the amplifier is \_\_\_\_\_

16. Consider the circuit given below



The value of input resistance  $R_{in}$  is \_\_\_\_\_  $k\Omega$

**Answers :**

1. b                      2. c                      3. d                      4. a                      5. 1.45 (1.20 – 2.00)                      6. 8.66 (7.80 – 9.10)  
 7. 53.75 (53.50 – 54.00)                      8. b                      9. a                      10. c                      11. a  
 12. a                      13. 100 (99.90 – 100.10)                      14. 0                      15. 5  
 16. 102.38 (102.00 – 102.50)